

U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.	
				M-10317-1D US		Unassigned	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s) 10/822/166			
(Use several sheets if necessary)				Jack H. Yuan and Jacob Haskell			
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U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>TL</u> ↓	A1	4,336,603	Jun. 22, 1982	Kotecha et al.			/
	A2	4,380,057	Apr. 12, 1983	Kotecha et al.			
	A3	4,417,264	Nov. 22, 1983	Angle			
	A4	4,477,825	Oct. 16, 1984	Yaron et al.			
	A5	4,855,955	Aug. 8, 1989	Cioaca			
	A6	4,885,719	Dec. 5, 1989	Brahmbhatt			
	A7	5,021,999	Jun. 4 1991	Kohda et al.			
	A8	5,043,940	Aug. 27, 1991	Harari			
	A9	5,047,362	Sep. 10, 1991	Bergemont			
	A10	5,070,032	Dec. 3, 1991	Yuan et al.			
↓	A11	5,095,344	Mar. 10, 1992	Harari			

Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
<u>TL</u> ↓	B1	55-43862	Mar. 27, 1980	Japan				Abs
	B2	0 051 158 B1	Oct. 5, 1981	Europe				
	B3	58-222561	Dec. 24, 1983	Japan			X	
	B4	WO 95/19047	Jul. 13, 1995	PCT				
	↓	B5	07-226449	Aug. 22, 1995	Japan			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
<u>TL</u>	C1	Alberts and Kotecha, "Multi-Bit Storage Fet Earom Cell", IBM Technical Disclosure Bulletin, Vol. 24, No. 7A, Dec. 1981, pp. 3311-3314.
<u>TL</u>	C2	Kamiya et al., "EPROM Cell With High Gate Injection Efficiency", Int'l Electron Devices Meeting Technical Digest, 1982, pp. 741-744.
<u>TL</u>	C3	Pein and Plummer, "Performance of the 3-D Sidewall Flash EPROM Cell", Int'l Electron Devices Meeting Technical Digest, 1993, pp. 2.1.1-3.5.4.

Examiner <u>Thule</u>	Date Considered <u>8/26/02</u>
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					M-10317-1D US		Unassigned	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant(s)		10/822,966	
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					Herewith		Unassigned	
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
TL	A12	5,095,461	Mar. 10, 1992	Miyakawa et al.			/	
	A13	5,159,570	Oct. 27, 1992	Mitchell et al.				
	A14	5,172,338	Dec. 15, 1992	Mehrotra et al.				
	A15	5,210,047	May 11, 1993	Woo et al.				
	A16	5,278,439	Jan. 11, 1994	Ma et al.				
	A17	5,297,148	Mar. 22, 1994	Harari et al.				
	A18	5,313,421	May 17, 1994	Guterman et al.				
	A19	5,315,541	May 24, 1994	Harari et al.				
	A20	5,343,063	Aug. 30, 1994	Yuan et al.				
	A21	5,364,806	Nov. 15, 1994	Ma et al.				
	A22	5,411,905	May 2, 1995	Acovic et al.				
	A23	5,412,600	May 2, 1995	Nakajima				
	A24	5,414,693	May 9, 1995	Ma et al.				
	A25	5,440,158	Aug. 8, 1995	Sung-Mu				
	A26	5,486,714	Jan. 23, 1996	Hong				
	A27	5,492,846	Feb. 20, 1996	Hara				
↓	A28	5,576,567	Nov. 19, 1996	Mori				
Foreign Patent Documents								
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		Document	Date	Country	Class	Subclass	Yes	No
	B6							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
TL	C4	Ma et al., "A Dual-bit Split-Gate EEPROM (DSG) Cell in Contactless Array for Single-Vcc High Density Flash Memories", Int'l Electron Devices Meeting Technical Digest, 1994, pp. 3.5.1-3.5.4.						
TL	C5	Kuo et al., "TEFET - A High Density, Low Erase Voltage, Trench Flash EEPROM, 1994 Symposium on VLSI Technology, pp. 51-52.						
Examiner		Date Considered						
Thurle		8/20/04						
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>TL</u>	A29	5,606,521	Feb. 25, 1997	Kuo et al.			
	A30	5,616,510	Apr. 1, 1997	Wong			
	A31	5,636,160	Jun. 3, 1997	Omino et al.			
	A32	5,643,814	Jul. 1, 1997	Chung			
	A33	B1 5,172,338	Jul. 8, 1997	Mehrotra et al.			
	A34	5,661,053	Aug. 26, 1997	Yuan			
	A35	5,712,180	Jan. 27, 1998	Guterman et al.			
	A36	5,714,412	Feb. 3, 1998	Liang et al.			
	A37	5,786,612	Jul. 28, 1998	Otani et al.			
	A38	5,812,449	Sep. 22, 1998	Song			
	A39	5,991,201	Nov. 23, 1999	Kuo et al.			
	A40	6,091,633	Jul. 18, 2000	Cerne et al.			
	A41	6,103,573	Aug. 15, 2000	Harari et al.			
	A42	6,151,248	Nov. 21, 2000	Harari et al.			
	A43	5,679,591	Oct. 21, 1997	Lin et al.			
	A44	6,329,685	Dec. 11, 2001	Lee			
✓	A45	5,851,879	Dec. 22, 1998	Lin et al.			
Foreign Patent Documents							
						Translation	
		Document	Date	Country	Class	Subclass	Yes No
	B7						
	B8						
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
	C6	PCT International Search Report, International Application No. PCT/US01/29405, Apr. 12, 2002, 3 pages.					
Examiner <u>Thao</u>		Date Considered <u>8/20/04</u>					
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